


☐ Pending

☒ Active

☒ L1: (2) "6117750"

☒ L2: (412523) semiconductor and substrate

☒ L3: (101) L2 and (threading adj dislocation)

☐ Failed

☒ (27) (((semiconductor and gate) and isotropic) and (not a

☒ (213) (((semiconductor and gate) and isotropic) and (not a

☒ DBs: ☐ USPAT; ☐ USPGPUB; ☐ EPO; ☐ JPO; ☐ DERWENT; ☐ IBM; ☐ TDB

☐ Plurals ☐ Synonyms

Default operator:

☒ Highlight all hit terms initially

	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRel
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20010040246 A1		23	GaN field-effect transistor and method of manufacturing the same		
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20010040244 A1		10	Relaxed InGaAs buffers		
3	<input type="checkbox"/>	<input type="checkbox"/>	US 20010039104 A1		29	Semiconductor substrate, light-emitting device, and method for		
4	<input type="checkbox"/>	<input type="checkbox"/>	US 20010039098 A1		10	Method for fabricating silicon-on-insulator material		
5	<input type="checkbox"/>	<input type="checkbox"/>	US 20010031385 A1		11	Group III-V compound semiconductor and method of produ		
6	<input type="checkbox"/>	<input type="checkbox"/>	US 20010030329 A1		30	Nitride compound semiconductor light emitting device and method for		
7	<input type="checkbox"/>	<input type="checkbox"/>	US 20010026873 A1		10	METHOD FOR PRODUCING HIGH QUALITY HETEROEPITAX		
8	<input type="checkbox"/>	<input type="checkbox"/>	US 20010024884 A1		10	Low threading dislocation density relaxed mismatched epilayers without		
9	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20010023946 A1		11	Crystal growth method for nitride semiconductor, nitride semiconducto		
10	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20010012678 A1		31	Method for the formation of semiconductor laver		

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Active

- L1: (2) "6117750"
- L2: (412523) semiconductor and substrate
- L3: (101) L2 and (threading adj dislocation)
- L4: (27) ((semiconductor and substrate) and lattice-mism)

Failed

- (27) (((semiconductor and gate) and isotropic) and (not &))
- (213) (((semiconductor and gate) and isotropic) and (not &))

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DBs: USPAT, US-PGPUB, EPO, JPO, DERWENT, IBM TDB

Default operator: OR

Highlight all hit terms initially

((semiconductor and substrate) and lattice-mismatched) and multilayer

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	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20010038655 A1		39	Semiconductor devices		
2	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6239354 B1	20010529	7	Electrical isolation of component cells in monolithically interconnected	136/249	136/244
3	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6222200 B1	20010424	13	Photodetector with spectrally extended responsivity	257/18	136/246 257/185 257/186
4	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6111276 A	20000829	8	Semiconductor device structures incorporating "buried" mirrors and/or	257/98	136/259 136/262
5	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6010937 A	20000104	10	Reduction of dislocations in a heteroepitaxial semiconductor structu	438/363	438/413 438/495
6	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5953356 A	19990914	18	Intersubband quantum box semiconductor laser	372/45	372/43
7	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5912913 A	19990615	20	Vertical cavity surface emitting laser, optical transmitter-receiver	372/45	372/46 372/50
8	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5883911 A	19990316	7	Surface-emitting laser device	372/45	372/96
9	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5874747 A	19990223	31	High brightness electroluminescent device emitting in the green to	257/77	257/103 257/461
10	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 5856206 A	19990105	6	Method for fabricating bragg reflector using in situ laser reflectometry	438/32	118/715 438/29